Dual NPN Bias Resistor Transistors R1 = 4.7 k Ω , R2 = 47 k Ω

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current - Continuous	Ic	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	5	Vdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ORDERING INFORMATION

Device	Package	Shipping [†]
MUN5233DW1T1G, SMUN5233DW1T1G	SOT-363	3,000/Tape & Reel
NSBC143ZDXV6T1G	SOT-563	4,000/Tape & Reel
NSBC143ZDXV6T5G	SOT-563	8,000/Tape & Reel
NSBC143ZDP6T5G	SOT-963	8,000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

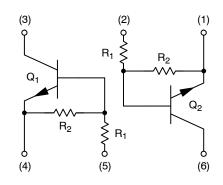
1



ON Semiconductor®

http://onsemi.com

PIN CONNECTIONS



MARKING DIAGRAMS



SOT-363 CASE 419B





SOT-563 CASE 463A





SOT-963 CASE 527AD



7K/Y = Specific Device Code

M = Date Code*
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

THERMAL CHARACTERISTICS

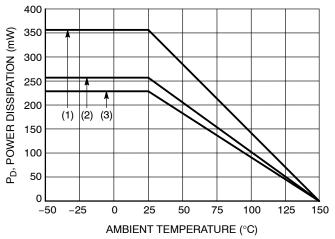
Characteristic		Symbol	Max	Unit
MUN5233DW1 (SOT-363) ONE JUNCTION HEATED				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	670 490	°C/W
MUN5233DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)	•		•	
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 325	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	188 208	°C/W
Junction and Storage Temperature Range		T_J , T_{stg}	-55 to +150	°C
NSBC143ZDXV6 (SOT-563) ONE JUNCTION HEATED				
Total Device Dissipation T _A = 25°C Derate above 25°C	(Note 1) (Note 1)	P_{D}	357 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	R_{\thetaJA}	350	°C/W
NSBC143ZDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation T _A = 25°C Derate above 25°C	(Note 1) (Note 1)	P_{D}	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	250	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
NSBC143ZDP6 (SOT-963) ONE JUNCTION HEATED				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 4) (Note 5) (Note 4) (Note 5)	P _D	231 269 1.9 2.2	MW mW/°C
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5)	$R_{ hetaJA}$	540 464	°C/W
NSBC143ZDP6 (SOT-963) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 4) (Note 5) (Note 4)	P_{D}	339 408 2.7	MW mW/°C
	(Note 5)		3.3	•
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5)	$R_{ hetaJA}$	369 306	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- FR-4 @ Millimum Fau.
 FR-4 @ 1.0 × 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.
 FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C, common for Q_1 and Q_2 , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	-	_	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	-	-	0.18	mAdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 6) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 6) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	80	200	-	
Collector-Emitter Saturation Voltage (Note 6) (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	-	-	0.25	V
Input Voltage (Off) (V _{CE} = 5.0 V, I _C = 100 μA)	V _{i(off)}	-	0.6	-	Vdc
Input Voltage (On) (V _{CE} = 0.2 V, I _C = 5.0 mA)	V _{i(on)}	-	0.9	-	Vdc
Output Voltage (On) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OL}	-	-	0.2	Vdc
Output Voltage (Off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R ₁ /R ₂	0.08	0.1	0.12	

^{6.} Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.



- (1) SOT-363; 1.0×1.0 Inch Pad
- (2) SOT-563; Minimum Pad
- (3) SOT–963; 100 mm², 1 oz. Copper Trace

Figure 1. Derating Curve

TYPICAL CHARACTERISTICS MUN5233DW1, NSBC143ZDXV6

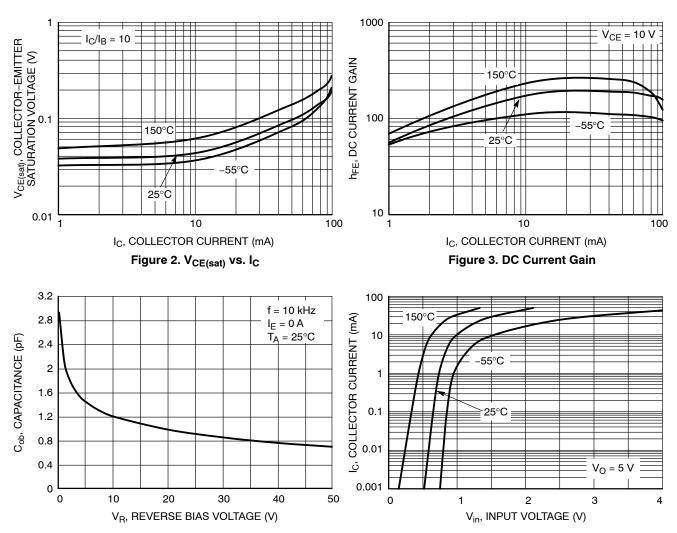


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

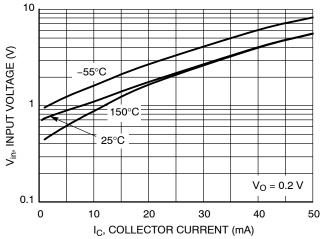


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS NSBC143ZDP6

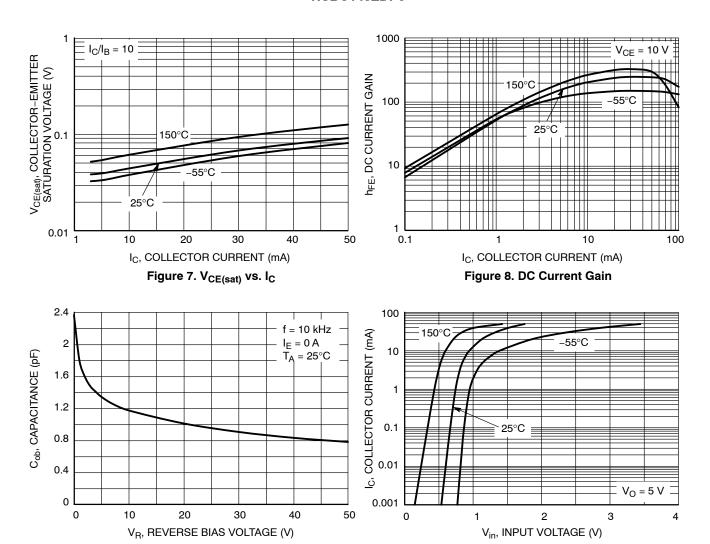


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

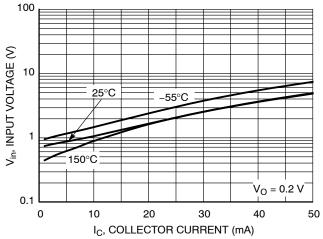
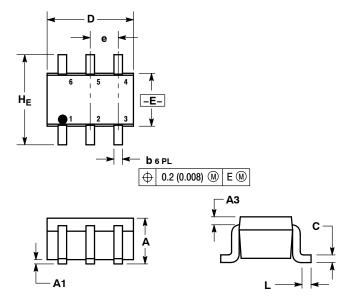


Figure 11. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

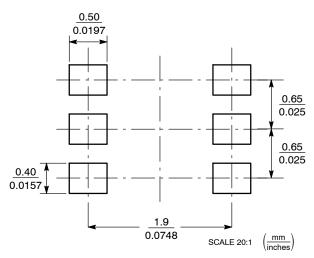
SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE W**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
А3		0.20 RE	F		0.008 RI	EF
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC		0	.026 BS	С	
L	0.10	0.20	0.30	0.004	0.008	0.012
He	2 00	2 10	2 20	0.078	0.082	0.086

SOLDERING FOOTPRINT*

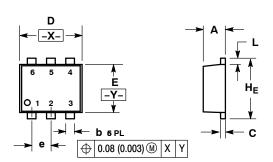


SC-88/SC70-6/SOT-363

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

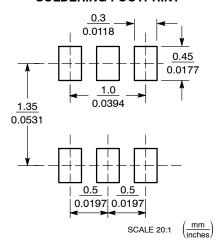
SOT-563, 6 LEAD CASE 463A **ISSUE F**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIN	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е		0.5 BSC)	C	0.02 BS0	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

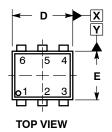
SOLDERING FOOTPRINT*

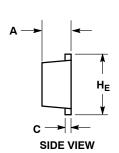


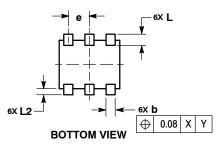
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-963 CASE 527AD **ISSUE E**





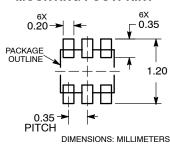


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
Е	0.75	0.80	0.85	
е	0.35 BSC			
Hε	0.95	1.00	1.05	
L	0.19 REF			
L2	0.05	0.10	0.15	

RECOMMENDED **MOUNTING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking, pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative